

L Number	Hits	Search Text	DB	Time stamp
1	838078	memory	USPAT; US-PGPUB; EPO; JPO	2003/01/12 11:36
2	8474	memory and (precharg\$4 or pre-charg\$4 or charg\$4) near3 (bit or bitline)	USPAT; US-PGPUB; EPO; JPO	2003/01/12 13:16
3	14	(memory and (precharg\$4 or pre-charg\$4 or charg\$4) near3 (bit or bitline)) and programmable near3 (resistor or resistance)	USPAT; US-PGPUB; EPO; JPO	2003/01/12 11:54
4	5	(memory and (precharg\$4 or pre-charg\$4 or charg\$4) near3 (bit or bitline)) and (writ\$4 or stor\$4) with programmable near3 (resistor or resistance)	USPAT; US-PGPUB; EPO; JPO	2003/01/12 11:54
5	128682	memory and (precharg\$4 or pre-charg\$4 or charg\$4)	USPAT; US-PGPUB; EPO; JPO	2003/01/12 11:54
6	289	(memory and (precharg\$4 or pre-charg\$4 or charg\$4)) and programmable near3 (resistor or resistance)	USPAT; US-PGPUB; EPO; JPO	2003/01/12 13:17
7	35	((memory and (precharg\$4 or pre-charg\$4 or charg\$4)) and programmable near3 (resistor or resistance)) and (writ\$4 or stor\$4) with programmable near3 (resistor or resistance)	USPAT; US-PGPUB; EPO; JPO	2003/01/12 11:54
8	30	((memory and (precharg\$4 or pre-charg\$4 or charg\$4)) and programmable near3 (resistor or resistance)) and (writ\$4 or stor\$4) with programmable near3 (resistor or resistance)) not ((memory and (precharg\$4 or pre-charg\$4 or charg\$4) near3 (bit or bitline)) and (writ\$4 or stor\$4) with programmable near3 (resistor or resistance))	USPAT; US-PGPUB; EPO; JPO	2003/01/12 13:09
9	10	((((memory and (precharg\$4 or pre-charg\$4 or charg\$4)) and programmable near3 (resistor or resistance)) and (writ\$4 or stor\$4) with programmable near3 (resistor or resistance)) not ((memory and (precharg\$4 or pre-charg\$4 or charg\$4) near3 (bit or bitline)) and (writ\$4 or stor\$4) with programmable near3 (resistor or resistance))) and capacitor	USPAT; US-PGPUB; EPO; JPO	2003/01/12 13:09
10	11	((((memory and (precharg\$4 or pre-charg\$4 or charg\$4)) and programmable near3 (resistor or resistance)) and (writ\$4 or stor\$4) with programmable near3 (resistor or resistance)) not ((memory and (precharg\$4 or pre-charg\$4 or charg\$4) near3 (bit or bitline)) and (writ\$4 or stor\$4) with programmable near3 (resistor or resistance))) and capacitance	USPAT; US-PGPUB; EPO; JPO	2003/01/12 13:09

11	14	((((memory and (precharg\$4 or pre-charg\$4 or charg\$4)) and programmable near3 (resistor or resistance)) and (writ\$4 or stor\$4) with programmable near3 (resistor or resistance)) not ((memory and (precharg\$4 or pre-charg\$4 or charg\$4) near3 (bit or bitline)) and (writ\$4 or stor\$4) with programmable near3 (resistor or resistance))) and capacitor) (((((memory and (precharg\$4 or pre-charg\$4 or charg\$4)) and programmable near3 (resistor or resistance)) and (writ\$4 or stor\$4) with programmable near3 (resistor or resistance)) not ((memory and (precharg\$4 or pre-charg\$4 or charg\$4) near3 (bit or bitline)) and (writ\$4 or stor\$4) with programmable near3 (resistor or resistance))) and capacitance)	USPAT; US-PGPUB; EPO; JPO	2003/01/12 13:10
12	2005	memory and (precharg\$4 or pre-charg\$4 or charg\$4) near3 (bit or bitline) with (capacitor or capacitance)	USPAT; US-PGPUB; EPO; JPO	2003/01/12 13:17
13	5	(memory and (precharg\$4 or pre-charg\$4 or charg\$4) near3 (bit or bitline) with (capacitor or capacitance)) and programmable near3 (resistor or resistance)	USPAT; US-PGPUB; EPO; JPO	2003/01/12 13:17

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1	838078	memory	USPAT; US-PGPUB; EPO; JPO	2003/01/12 11:36
2	8474	memory and (precharg\$4 or pre-charg\$4 or charg\$4) near3 (bit or bitline)	USPAT; US-PGPUB; EPO; JPO	2003/01/12 14:08
3	14	(memory and (precharg\$4 or pre-charg\$4 or charg\$4) near3 (bit or bitline)) and programmable near3 (resistor or resistance)	USPAT; US-PGPUB; EPO; JPO	2003/01/12 11:54
4	5	(memory and (precharg\$4 or pre-charg\$4 or charg\$4) near3 (bit or bitline)) and (writ\$4 or stor\$4) with programmable near3 (resistor or resistance)	USPAT; US-PGPUB; EPO; JPO	2003/01/12 11:54
5	128682	memory and (precharg\$4 or pre-charg\$4 or charg\$4)	USPAT; US-PGPUB; EPO; JPO	2003/01/12 11:54
6	289	(memory and (precharg\$4 or pre-charg\$4 or charg\$4)) and programmable near3 (resistor or resistance)	USPAT; US-PGPUB; EPO; JPO	2003/01/12 13:17
7	35	((memory and (precharg\$4 or pre-charg\$4 or charg\$4)) and programmable near3 (resistor or resistance)) and (writ\$4 or stor\$4) with programmable near3 (resistor or resistance)	USPAT; US-PGPUB; EPO; JPO	2003/01/12 11:54
8	30	((memory and (precharg\$4 or pre-charg\$4 or charg\$4)) and programmable near3 (resistor or resistance)) and (writ\$4 or stor\$4) with programmable near3 (resistor or resistance)) not ((memory and (precharg\$4 or pre-charg\$4 or charg\$4) near3 (bit or bitline)) and (writ\$4 or stor\$4) with programmable near3 (resistor or resistance))	USPAT; US-PGPUB; EPO; JPO	2003/01/12 13:09
9	10	((((memory and (precharg\$4 or pre-charg\$4 or charg\$4)) and programmable near3 (resistor or resistance)) and (writ\$4 or stor\$4) with programmable near3 (resistor or resistance)) not ((memory and (precharg\$4 or pre-charg\$4 or charg\$4) near3 (bit or bitline)) and (writ\$4 or stor\$4) with programmable near3 (resistor or resistance))) and capacitor	USPAT; US-PGPUB; EPO; JPO	2003/01/12 13:09
10	11	((((memory and (precharg\$4 or pre-charg\$4 or charg\$4)) and programmable near3 (resistor or resistance)) and (writ\$4 or stor\$4) with programmable near3 (resistor or resistance)) not ((memory and (precharg\$4 or pre-charg\$4 or charg\$4) near3 (bit or bitline)) and (writ\$4 or stor\$4) with programmable near3 (resistor or resistance))) and capacitance	USPAT; US-PGPUB; EPO; JPO	2003/01/12 13:09

11	14	((((memory and (precharg\$4 or pre-charg\$4 or charg\$4)) and programmable near3 (resistor or resistance)) and (writ\$4 or stor\$4) with programmable near3 (resistor or resistance)) not ((memory and (precharg\$4 or pre-charg\$4 or charg\$4) near3 (bit or bitline)) and (writ\$4 or stor\$4) with programmable near3 (resistor or resistance))) and capacitor) (((((memory and (precharg\$4 or pre-charg\$4 or charg\$4)) and programmable near3 (resistor or resistance)) and (writ\$4 or stor\$4) with programmable near3 (resistor or resistance)) not ((memory and (precharg\$4 or pre-charg\$4 or charg\$4) near3 (bit or bitline)) and (writ\$4 or stor\$4) with programmable near3 (resistor or resistance))) and capacitance)	USPAT; US-PGPUB; EPO; JPO	2003/01/12 13:10
12	2005	memory and (precharg\$4 or pre-charg\$4 or charg\$4) near3 (bit or bitline) with (capacitor or capacitance)	USPAT; US-PGPUB; EPO; JPO	2003/01/12 13:17
13	5	(memory and (precharg\$4 or pre-charg\$4 or charg\$4) near3 (bit or bitline) with (capacitor or capacitance)) and programmable near3 (resistor or resistance)	USPAT; US-PGPUB; EPO; JPO	2003/01/12 13:17
14	6	(memory and (precharg\$4 or pre-charg\$4 or charg\$4) near3 (bit or bitline)) and programmable with memory with resistance	USPAT; US-PGPUB; EPO; JPO	2003/01/12 14:43
15	838078	(memory and (precharg\$4 or pre-charg\$4 or charg\$4) near3 (bit or bitline)) and programm\$4 with resist\$6 memory	USPAT; US-PGPUB; EPO; JPO	2003/01/12 14:44
16	56	(memory and (precharg\$4 or pre-charg\$4 or charg\$4) near3 (bit or bitline)) and programm\$4 with resist\$6 with memory	USPAT; US-PGPUB; EPO; JPO	2003/01/12 14:51
17	85	(memory and (precharg\$4 or pre-charg\$4 or charg\$4) near3 (bit or bitline)) and programm\$4 near3 resist\$6	USPAT; US-PGPUB; EPO; JPO	2003/01/12 14:52
18	27	(memory and (precharg\$4 or pre-charg\$4 or charg\$4) near3 (bit or bitline)) and programm\$4 near3 resist\$6 with (voltage or potential)	USPAT; US-PGPUB; EPO; JPO	2003/01/12 15:01
19	113	(365/148).CCLS.	USPAT; US-PGPUB; EPO; JPO	2003/01/12 15:01
20	5768	((365/148).CCLS.) and precharg\$5 or pre-charg\$5	USPAT; US-PGPUB; EPO; JPO	2003/01/12 15:02
21	17	((365/148).CCLS.) and (precharg\$5 or pre-charg\$5)	USPAT; US-PGPUB; EPO; JPO	2003/01/12 15:06
22	10	((365/148).CCLS.) and (precharg\$5 or pre-charg\$5 or charg\$5) with (bit or bitline) with (program\$5 or writ\$4 or stor\$5)	USPAT; US-PGPUB; EPO; JPO	2003/01/12 15:08